

GaAlAs T-1 3/4 PACKAGE INFRARED EMITTING DIODE

MIE-526L3U

Description

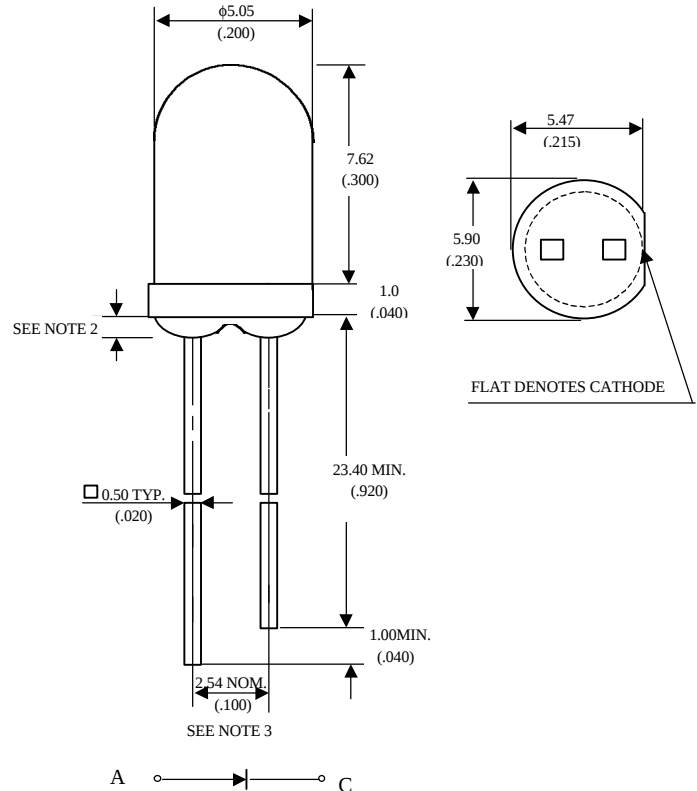
The MIE-526L3U is infrared emitting diodes in GaAlAs technology molded in pastel blue transparent package.

Features

- Suitable for DC and high pulse current operation
- Standard T-1 3/4 (ϕ 5mm) package
- Peak wavelength $\lambda_p = 880$ nm
- Good spectral matching to si-photodetector
- Radiant angle : 20°

Package Dimensions

Unit: mm (inches)



Notes :

1. Tolerance is ± 0.25 mm (.010") unless otherwise noted.
2. Protruded resin under flange is 1.5 mm (.059") max.
3. Lead spacing is measured where the leads emerge from the package.

Absolute Maximum Ratings

@ $T_A = 25^\circ\text{C}$

Parameter	Maximum Rating	Unit
Power Dissipation	120	mW
Peak Forward Current(300pps,10 μ s pulse)	1	A
Continuos Forward Current	100	mA
Reverse Voltage	5	V
Operating Temperature Range	-55°C to $+100^\circ\text{C}$	
Storage Temperature Range	-55°C to $+100^\circ\text{C}$	
Lead Soldering Temperature	260 $^\circ\text{C}$ for 5 seconds	

UNi

Unity Opto Technology Co., Ltd.

11/18/2000

Optical-Electrical Characteristics

'@ T_A=25°C

Parameter	Test Conditions	Symbol	Min.	Typ .	Max.	Unit
Radiant Intensity	I _F =20mA	I _e		2.4	-	mW/sr
Forward Voltage	I _F =50mA	V _F		1.4	1.7	V
	I _F =200mA			1.85	2.10	
Reverse Current	V _R = 5V	I _R			100	μA
Peak Wavelength	I _F =20mA	λ		880		nm
Spectral Bandwidth	I _F =20mA	Δλ		60		nm
View Angle	I _F =20mA	2θ _{1/2}	-	20	-	deg.

Typical Optical-Electrical Characteristic Curves

